General Purpose Transistors

PNP Bipolar Junction Transistor

(Complementary NPN Device: MMBT2132T1/T3)

NOTE: Voltage and Current are negative for the PNP Transistor.

MAXIMUM RATINGS ($T_C = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	30	V
Collector-Base Voltage	V _{CBO}	40	V
Emitter-Base Voltage	V _{EBO}	5.0	V
Collector Current	I _C	700	mA
Base Current	I _B	350	mA
Total Power Dissipation @ $T_C = 25^{\circ}C$ Total Power Dissipation @ $T_C = 85^{\circ}C$ Thermal Resistance – Junction–to–Ambient (Note 1)	P _D P _D R _{θJA}	342 178 366	mW °C/W
Total Power Dissipation @ T _C = 25°C Total Power Dissipation @ T _C = 85°C Thermal Resistance – Junction–to–Ambient (Note 2)	P _D P _D R _{θJA}	665 346 188	mW mW °C/W
Operating and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

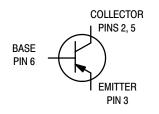
- 1. Minimum FR-4 or G-10 PCB, Operating to Steady State.
- Mounted onto a 2" square FR-4 Board (1" sq. 2 oz Cu 0.06" thick single sided), Operating to Steady State.

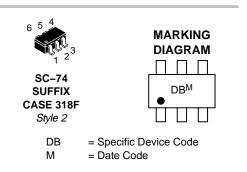


ON Semiconductor®

http://onsemi.com

0.7 AMPERES 30 VOLTS – V_{(BR)CEO} 342 mW





ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT2131T1	SC-74	3000/Tape & Reel

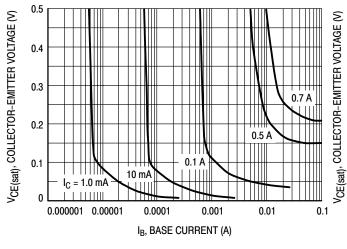
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

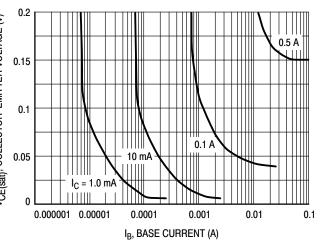
Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector - Base Breakdown Voltage	$(I_C = 100 \mu A)$	V _{(BR)CBO}	40	_	_	V
Collector – Emitter Breakdown Voltage (I _C = 10 mA)		V _{(BR)CEO}	30	_	_	V
Emitter-Base Breakdown Voltage	$(I_E = 100 \mu A)$	V _{(BR)EBO}	5.0	_	_	V
Collector Cutoff Current (V _C	$(V_{CB} = 25 \text{ V}, I_E = 0 \text{ A})$ $B = 25 \text{ V}, I_E = 0 \text{ A}, T_A = 125^{\circ}\text{C})$	I _{CBO}	- -	- -	1.0 10	μΑ
Emitter Cutoff Current	$(V_{EB} = 5.0 \text{ V}, I_{C} = 0 \text{ A})$	I _{EBO}	-	_	10	μΑ
ON CHARACTERISTICS						
DC Current Gain	$(V_{CE} = 3.0 \text{ V}, I_{C} = 100 \text{ mA})$	h _{FE}	150	_	_	V
Collector - Emitter Saturation Voltage	$(I_C = 500 \text{ mA}, I_B = 50 \text{ mA})$	V _{CE(sat)}	_	_	0.25	V
Collector - Emitter Saturation Voltage	$(I_C = 700 \text{ mA}, I_B = 70 \text{ mA})$	V _{CE(sat)}	-	_	0.4	V
Base–Emitter Saturation Voltage	$(I_C = 700 \text{ mA}, I_B = 70 \text{ mA})$	V _{BE(sat)}	-	_	1.1	V
		+		+	+	

V_{BE(on)}

 $(I_C = 700 \text{ mA}, V_{CE} = 1.0 \text{ V})$



Collector-Emitter Saturation Voltage

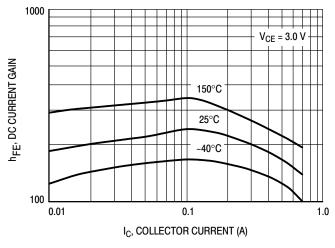


1.0

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Figure 1. Collector Saturation Region

Figure 2. Collector Saturation Region





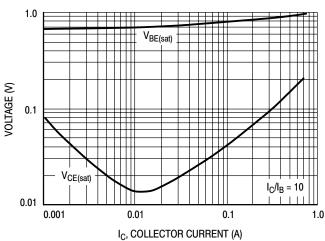


Figure 4. "ON" Voltages

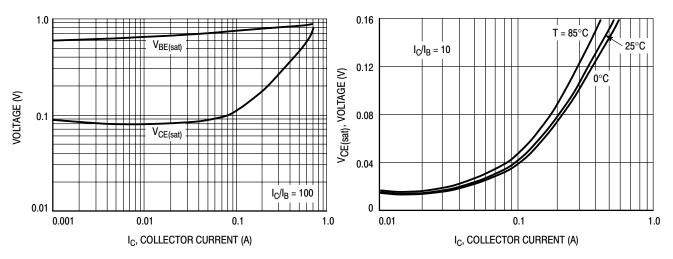


Figure 5. "ON" Voltages

Figure 6. Collector-Emitter Saturation Voltage

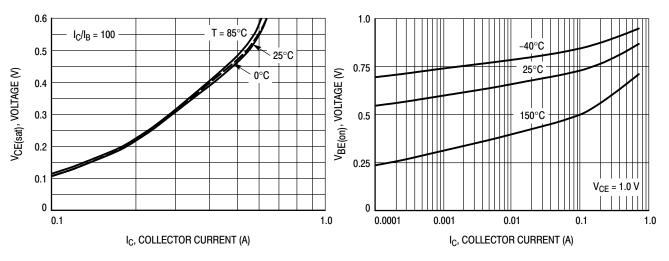


Figure 7. Collector-Emitter Saturation Voltage

Figure 8. V_{BE(on)} Voltage

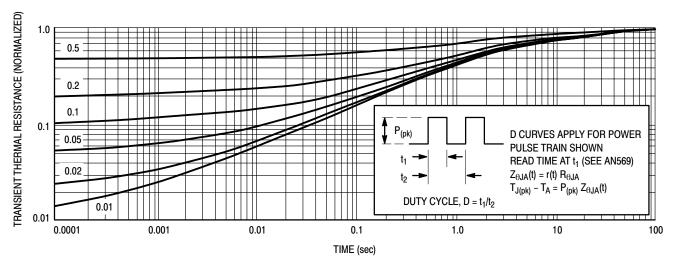
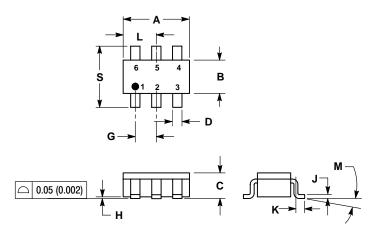


Figure 9. Thermal Response Curve

PACKAGE DIMENSIONS

SC-74 CASE 318F-05 ISSUE K



- NOTES:
 1. DIMENSIONING AND TOLERANCING
- PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM
- THICKNESS OF BASE MATERIAL. 318F-01, -02, -03 OBSOLETE. NEW STANDARD 318F-04.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.1142	0.1220	2.90	3.10	
В	0.0512	0.0669	1.30	1.70	
С	0.0354	0.0433	0.90	1.10	
D	0.0098	0.0197	0.25	0.50	
G	0.0335	0.0413	0.85	1.05	
Н	0.0005	0.0040	0.013	0.100	
J	0.0040	0.0102	0.10	0.26	
K	0.0079	0.0236	0.20	0.60	
L	0.0493	0.0649	1.25	1.65	
M	0 °	10°	0 °	10°	
S	0.0985	0.1181	2.50	3.00	

- STYLE 2: PIN 1. NO CONNECTION
 - 2. COLLECTOR
 - 3. EMITTER
 - 4. NO CONNECTION
 - 5. COLLECTOR 6. BASE

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